

Silicon NPN Power Transistors

2SD401A

DESCRIPTION

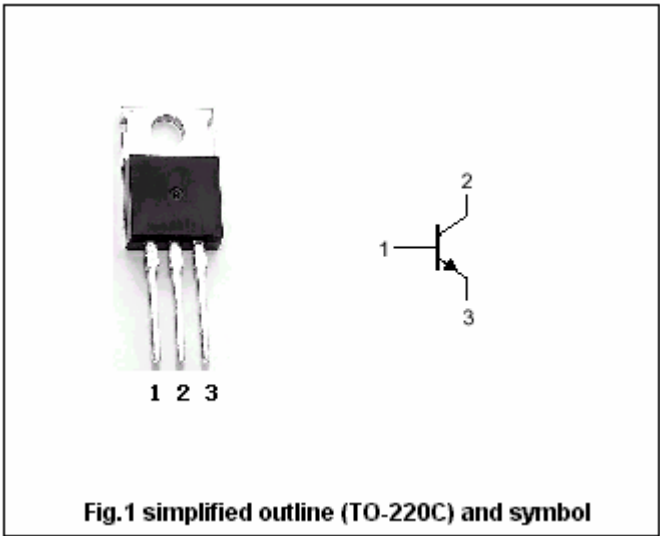
- With TO-220C package
- Complement to type 2SB546A
- Collector current $I_C=2A$
- Collector-collector voltage: $V_{CEO}=150V(\text{Min})$

APPLICATIONS

- For use in general purpose power amplifier, vertical output application

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		2	A
I_{CM}	Collector current-peak		3	A
P_D	Total power dissipation	$T_C=25^\circ\text{C}$	25	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	CHARACTERISTICS	MAX	UNIT
$R_{\theta jc}$	Thermal resistance junction to case	5.0	$^\circ\text{C}/W$

Silicon NPN Power Transistors**2SD401A****CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA; I _B =0	150			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =0.5mA; I _E =0	200			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =0.5mA; I _B =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =500mA; I _B =50mA			1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =150V; I _E =0			50	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			50	μA
h _{FE}	DC current gain	I _C =0.4A; V _{CE} =10V	40		200	
f _T	Transition frequency	I _C =0.4A; V _{CE} =10V; f=1MHz		5		MHz

◆ h_{FE} classifications

M	L	K
40-80	60-120	100-200

Silicon NPN Power Transistors

2SD401A

PACKAGE OUTLINE

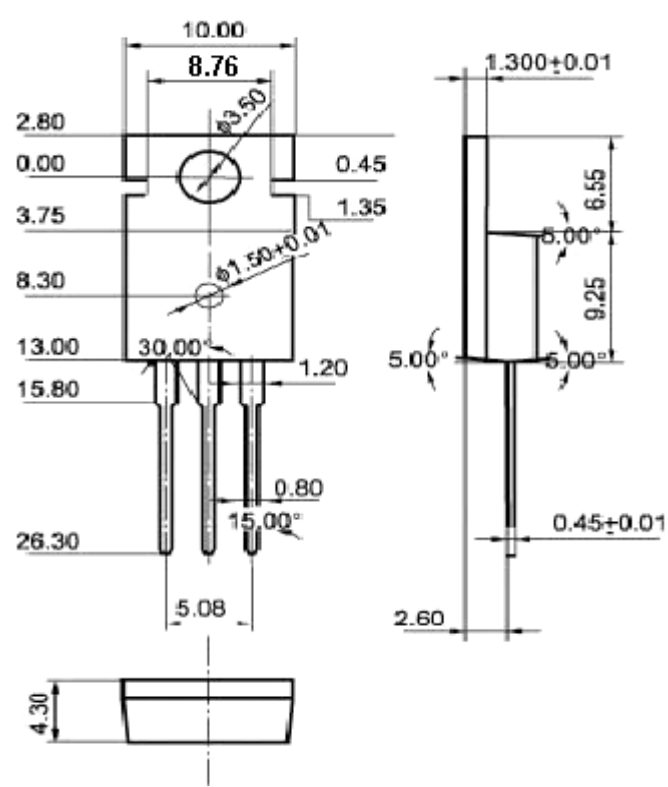


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)